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Enhancement of electrical parameters in solar grade monocrystalline silicon by external gettering through sacrificial silicon nanowire layer

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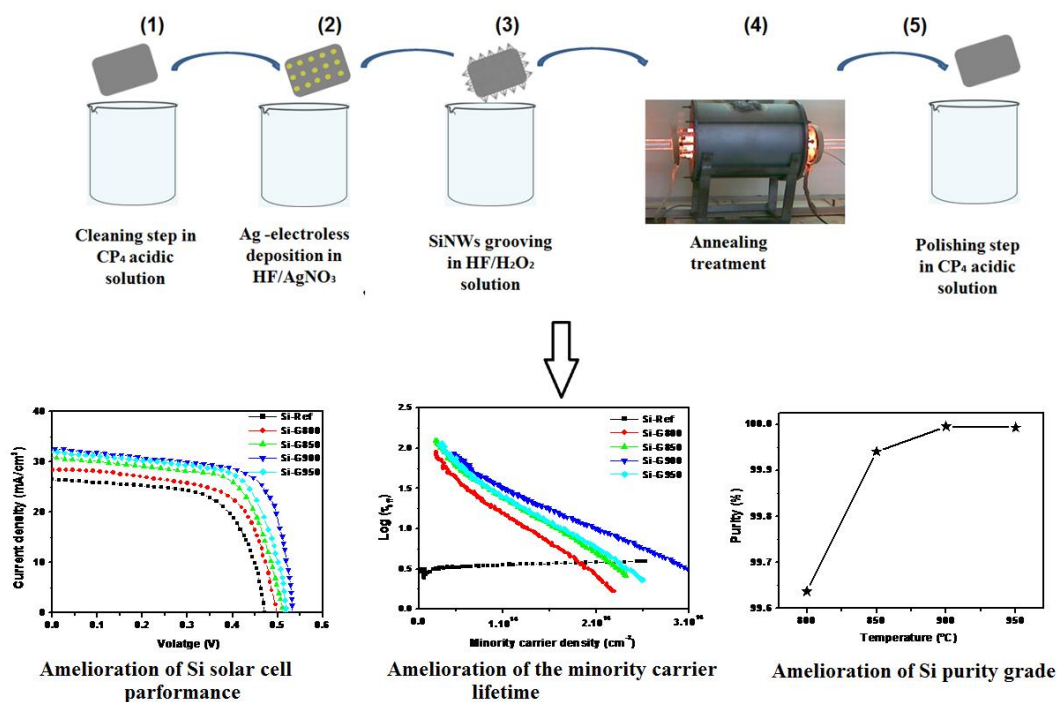
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Graphical abstract



Highlights

- ICP-AES analysis reveals a significant decrease in the metallic impurity concentration of silicon after the nanowire-based gettering process.
- Gettering process ameliorates the transport parameters of silicon substrates.

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